

High Voltage IGBT

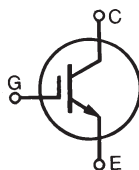
IXGT6N170AHV

$$V_{CES} = 1700V$$

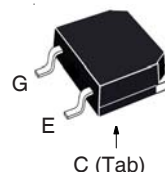
$$I_{C25} = 6A$$

$$V_{CE(sat)} \leq 7.0V$$

$$t_{fi(typ)} = 32ns$$



TO-268



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	6	A
I_{C110}	$T_C = 110^\circ C$	3	A
I_{CM}	$T_C = 25^\circ C$, 1ms	14	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 33\Omega$	$I_{CM} = 12$	A
(RBSOA)	Clamped Inductive Load	$0.8 \cdot V_{CES}$	
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 1200V$, $T_J = 125^\circ C$ $R_G = 33\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ C$	75	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ C$
Weight		4	g

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			10 μA 500 μA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 3A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		5.4	7.0 V V

Features

- High Blocking Voltage
- High Voltage Package

Advantages

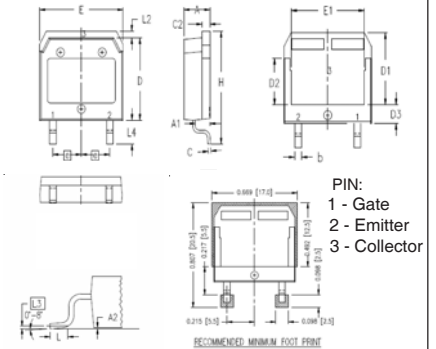
- High Power Density
- Easy to Mount

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 6\text{A}, V_{CE} = 20\text{V}$, Note 1	2.0	3.5	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		390	pF
C_{oes}			20	pF
C_{res}			7	pF
$Q_{g(on)}$	$I_C = 6\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		18.5	nC
Q_{ge}			2.8	nC
Q_{gc}			8.2	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 6\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 33\Omega$ Note 2		46	ns
t_{ri}			40	ns
E_{on}			0.59	mJ
$t_{d(off)}$			220	400 ns
t_{fi}			32	ns
E_{off}			0.18	0.36 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 6\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 33\Omega$ Note 2		48	ns
t_{ri}			43	ns
E_{on}			0.62	mJ
$t_{d(off)}$			230	ns
t_{fi}			41	ns
E_{off}			0.25	mJ
R_{thJC}				1.65 $^\circ\text{C/W}$

TO-268 (VHV) Outline



SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
E	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

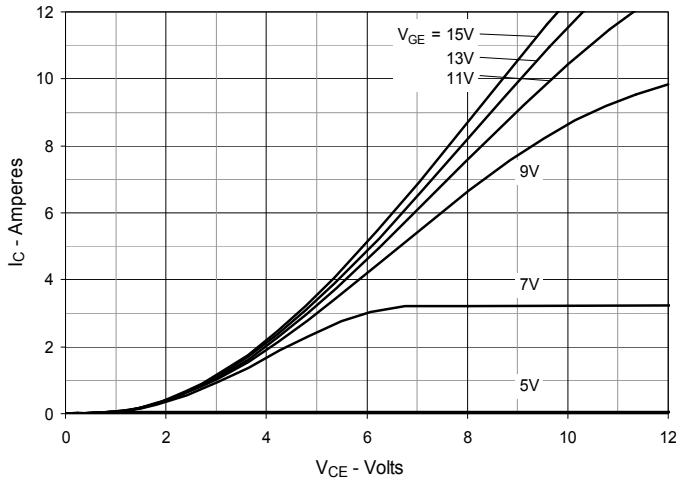


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

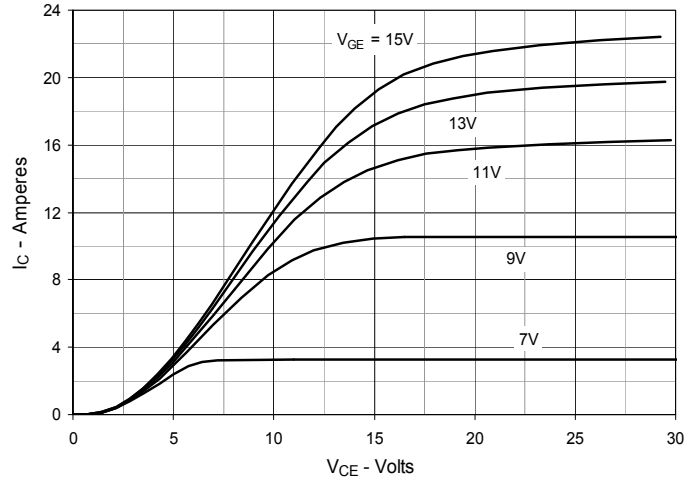


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

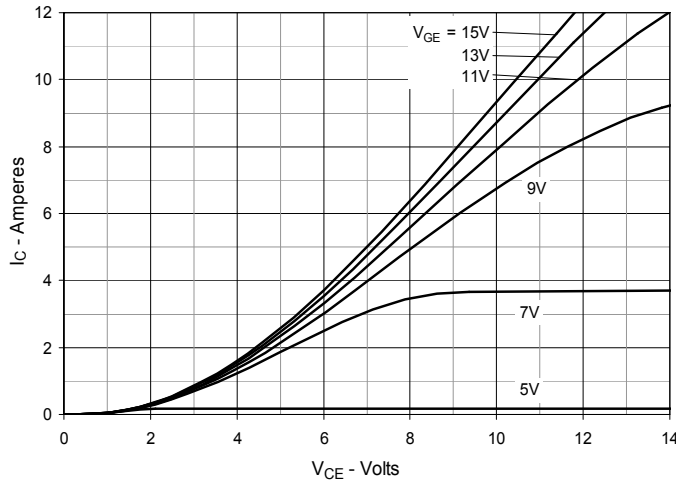


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

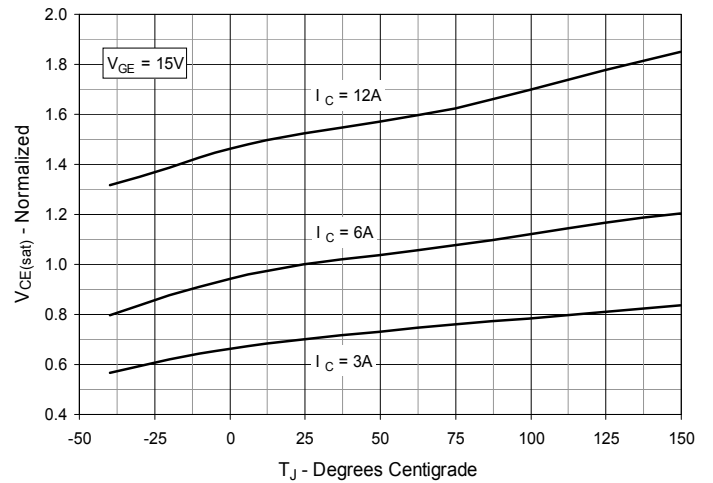


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

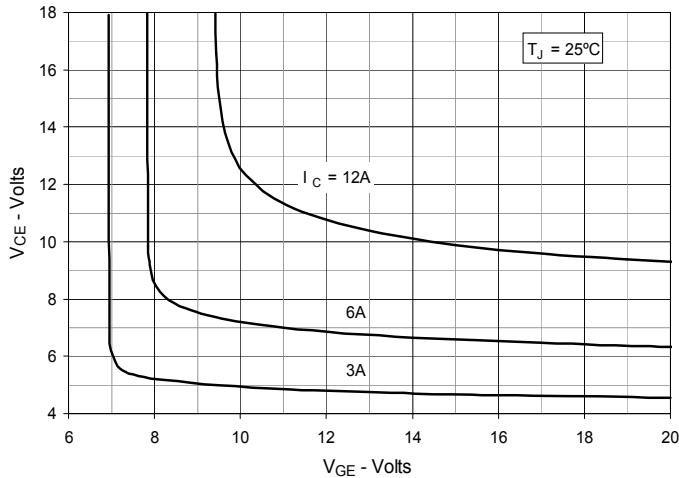


Fig. 6. Input Admittance

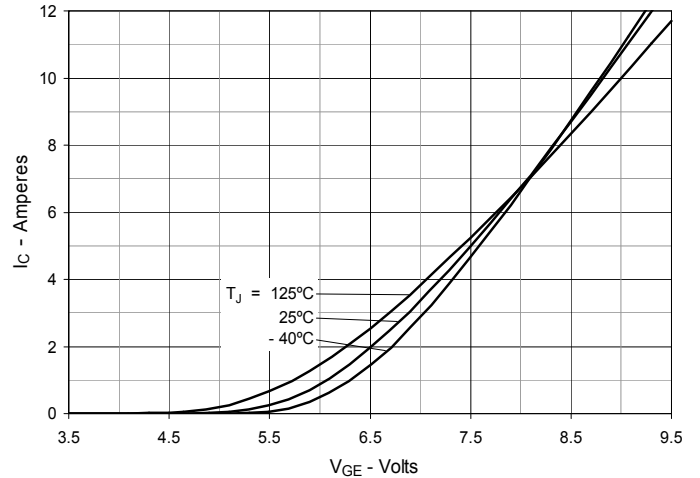


Fig. 7. Transconductance

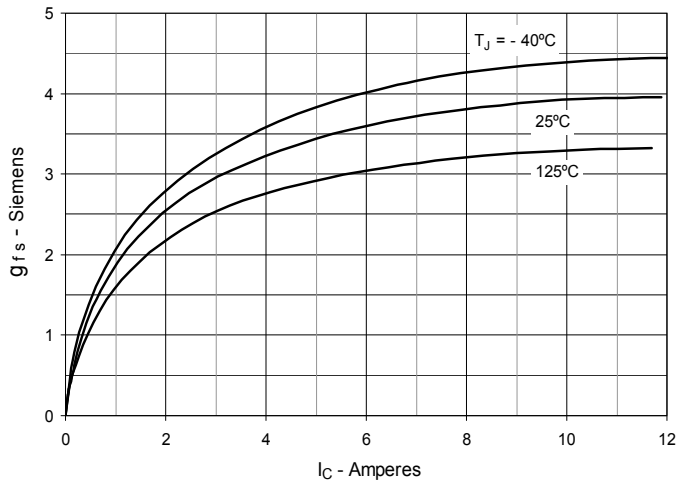


Fig. 8. Gate Charge

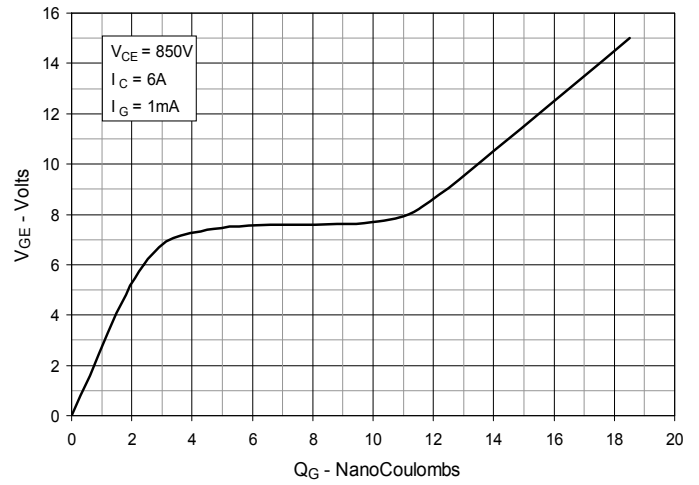


Fig. 9. Reverse-Bias Safe Operating Area

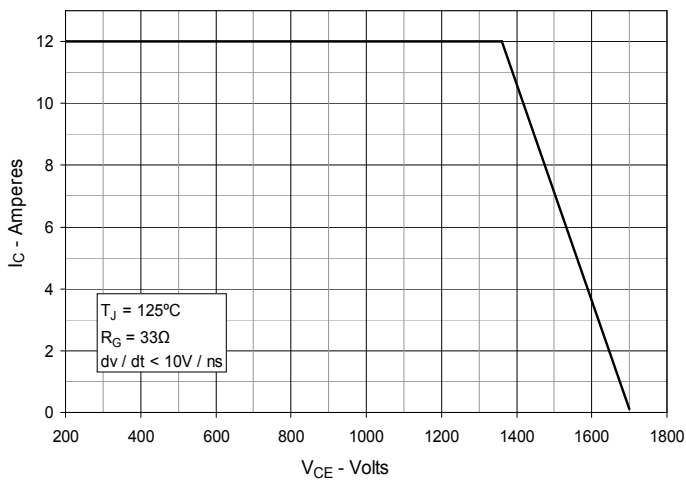


Fig. 10. Capacitance

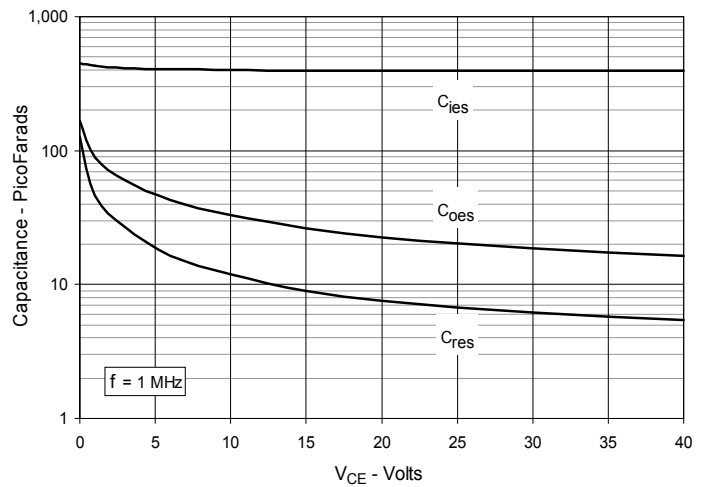


Fig. 11. Maximum Transient Thermal Impedance

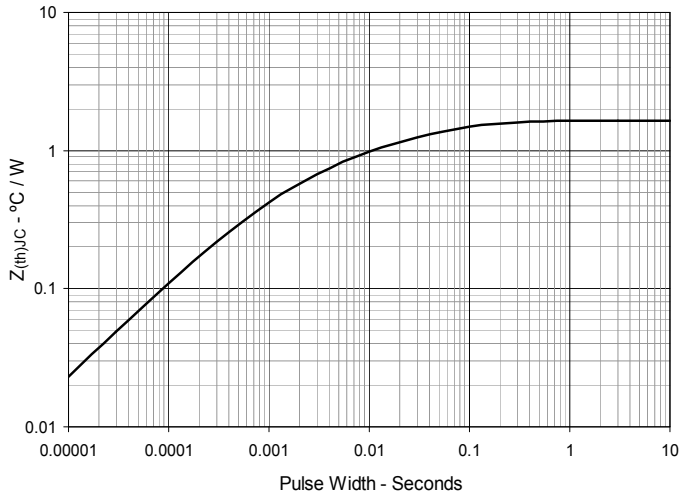


Fig. 12. Forward-Bias Safe Operating Area

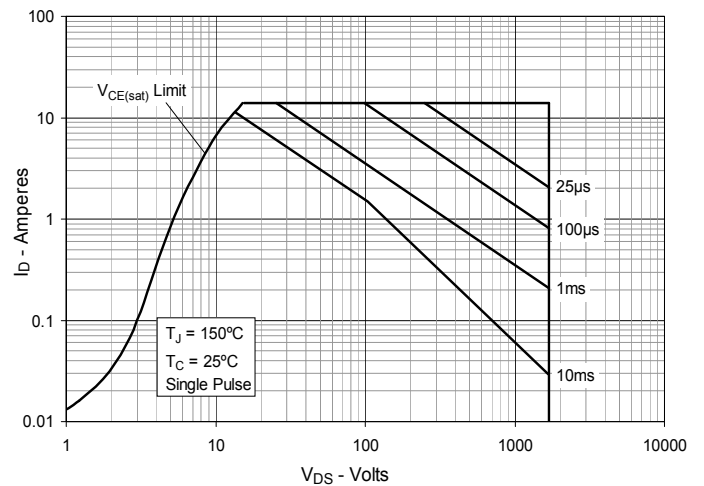


Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

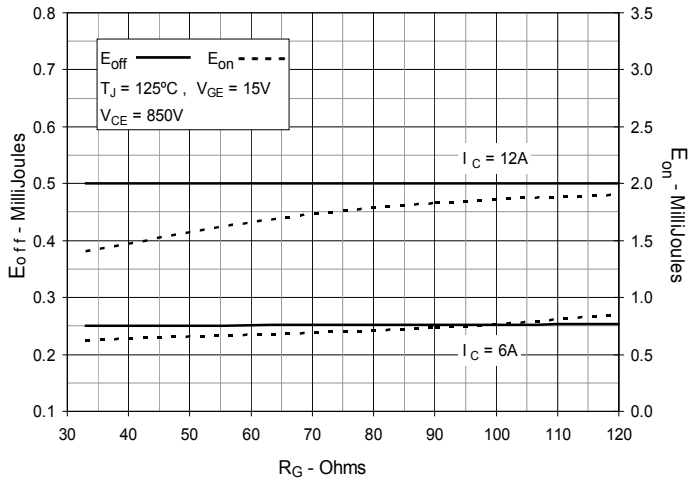


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

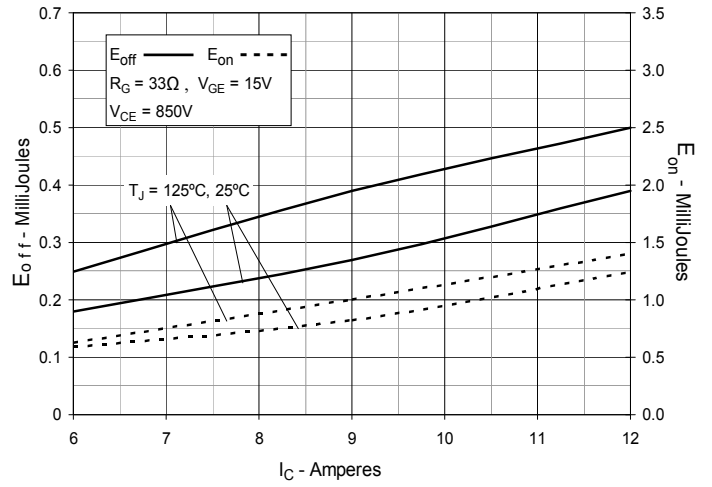


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

